

# 3-to-8 Line Decoder MC74VHC138

The MC74VHC138 is an advanced high speed CMOS 3-to-8 decoder fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

When the device is enabled, three Binary Select inputs (A0 - A2) determine which one of the outputs  $(\overline{Y0} - \overline{Y7})$  will go Low. When enable input E3 is held Low or either  $\overline{E2}$  or  $\overline{E1}$  is held High, decoding function is inhibited and all outputs go high. E3,  $\overline{E2}$ , and  $\overline{E1}$  inputs are provided to ease cascade connection and for use as an address decoder for memory systems.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

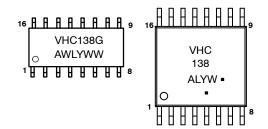
- High Speed:  $t_{PD} = 5.7 \text{ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A \text{ (Max)}$  at  $T_A = 25 \text{ °C}$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 122 FETs or 30.5 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant





SOIC-16 D SUFFIX CASE 751B TSSOP-16 DT SUFFIX CASE 948F

#### **MARKING DIAGRAM**



VHC138 = Specific Device Code

A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

#### ORDERING INFORMATION

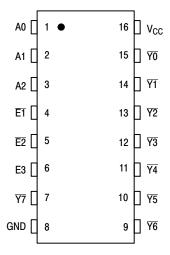
Device	Package	Shipping <sup>†</sup>
MC74VHC138DR2G	SOIC-16	2500 / Tape & Reel
MC74VHC138DTR2G	TSSOP-16	2500 / Tape & Reel

#### **DISCONTINUED** (Note 1)

	MC74VHC138DG	SOIC-16	48 Units / Tube
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- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- DISCONTINUED: This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

#### **PIN ASSIGNMENT**

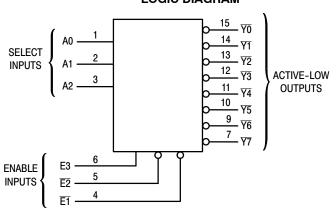


#### **FUNCTION TABLE**

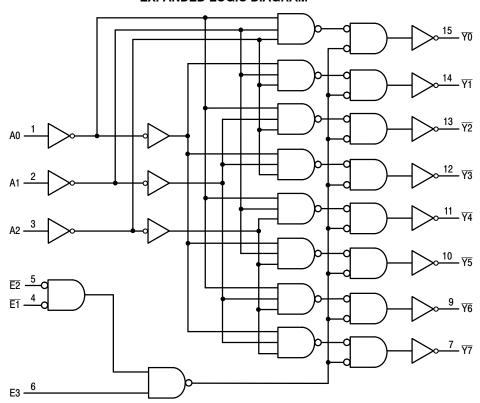
	Inputs					Outputs							
E3	E2	E1	A2	<b>A</b> 1	Α0	Y0	<b>Y</b> 1	Y2	<b>Y3</b>	<b>Y</b> 4	Y5	Y6	<b>Y</b> 7
Х	Х	Н	Х	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Τ
X	Н	Χ	X	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н
L	Χ	Χ	Х	Χ	Χ	Н	Н	Н	Н	Η	Н	Н	Н
Н	L	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н
Н	L	L	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н
Н	L	L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н
Н	L	L	L	Н	Н	Н	Н	Н	L	Н	Н	Н	Н
Н	L	L	Н	L	L	Н	Н	Н	Н	L	Н	Н	Η
Н	L	L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н
Н	L	L	Н	Η	L	Н	Н	Н	Н	Н	Н	L	Н
Н	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L

H = high level (steady state); L = low level (steady state); X = don't care

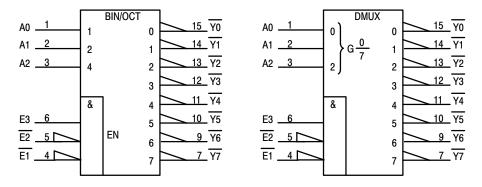
#### **LOGIC DIAGRAM**



#### **EXPANDED LOGIC DIAGRAM**



#### **IEC LOGIC DIAGRAM**



#### **MAXIMUM RATINGS\***

Symbol	Parameter	•	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	- 0.5 to + 7.0	V	
V <sub>in</sub>	DC Input Voltage	- 0.5 to + 7.0	V	
V <sub>out</sub>	DC Output Voltage	$-$ 0.5 to $V_{CC}$ + 0.5	V	
I <sub>IK</sub>	Input Diode Current	- 20	mA	
lok	Output Diode Current	±[ <b>2</b> 0	mA	
I <sub>out</sub>	DC Output Current, per Pin	±[ <b>2</b> 5	mA	
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GI	±[ <b>7</b> 5	mA	
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature		- 65 to + 150	°C

<sup>\*</sup> Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage		2.0	5.5	V
V <sub>in</sub>	DC Input Voltage		0	5.5	V
V <sub>out</sub>	DC Output Voltage		0	$V_{CC}$	V
T <sub>A</sub>	Operating Temperature		- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>		3.3V ±0.3V 5.0V ±0.5V	0 0	100 20	ns/V

The  $\theta_{JA}$  of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

## DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

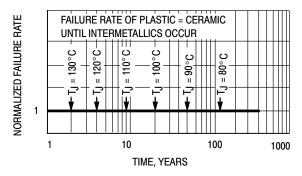


Figure 1. Failure Rate vs. Time Junction Temperature

<sup>†</sup>Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>		T <sub>A</sub> = 25°C	;	T <sub>A</sub> = ≤	85°C	<b>T</b> <sub>A</sub> = ≤	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		٧
		$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
	$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 4$ mA $I_{OL} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	-
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±[0.1		± <u>1</u> 1.0		±[1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0		40.0	μΑ

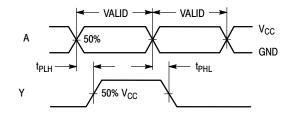
#### AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$ )

Symbo				-	T <sub>A</sub> = 25°C	;	T <sub>A</sub> = -	· 40 to °C	T <sub>A</sub> = -	55 to 5°C	
ı	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		8.2 10.0	11.4 15.8	1.0 1.0	13.5 18.0	1.0 1.0	13.5 18.0	ns
A to Y	A to Y	$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		5.7 7.2	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		8.1 10.6	12.8 16.3	1.0 1.0	15.0 18.5	1.0 1.0	15.0 18.5	ns
	E3 to Y	$V_{CC} = 5.0 \pm 0.5 V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		5.6 7.1	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		8.2 10.7	11.4 14.9	1.0 1.0	13.5 17.0	1.0 1.0	13.5 17.0	ns
	E2 or E1 to Y	$V_{CC} = 5.0 \pm 0.5 V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		5.8 7.3	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
C <sub>IN</sub>	Maximum Input Capacitance				4	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
$C_{PD}$	Power Dissipation Capacitance (Note 1)	34	pF

<sup>1.</sup>  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

### **SWITCHING WAVEFORMS**



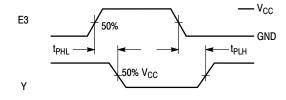
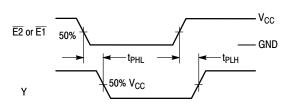
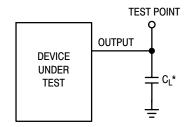


Figure 2.

Figure 3.







\*Includes all probe and jig capacitance

Figure 5. Test Circuit

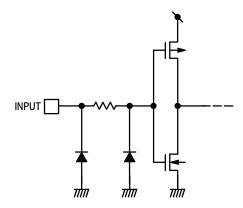


Figure 6. Input Equivalent Circuit



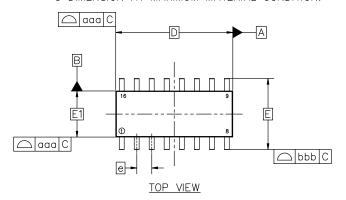


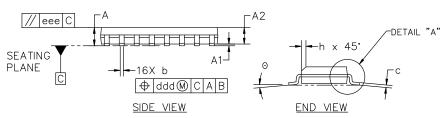
#### SOIC-16 9.90x3.90x1.37 1.27P CASE 751B ISSUE M

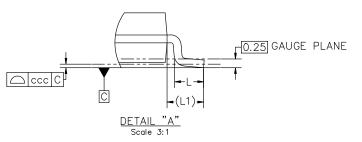
**DATE 18 OCT 2024** 

#### NOTES:

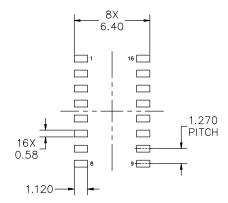
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- 5. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







	MILLIMETERS							
DIM	MIN	NOM	MAX					
А	1.35	1.55	1.75					
A1	0.10	0.18	0.25					
A2	1.25	1.37	1.50					
b	0.35	0.42	0.49					
С	0.19	0.22	0.25					
D		9.90 BSC						
E	6.00 BSC							
E1	3.90 BSC							
е	1.27 BSC							
h	0.25 0.50							
L	0.40 0.83 1.25							
L1	1.05 REF							
Θ	0 7.							
TOLERAN	CE OF FORM AND POSITION							
aaa	0.10							
bbb	0.20							
ccc	0.10							
ddd		0.25	·					
eee		0.10						



#### RECOMMENDED MOUNTING FOOTPRINT

\*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERRM/D

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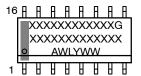
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#### **SOIC-16 9.90x3.90x1.37 1.27P** CASE 751B

ISSUE M

**DATE 18 OCT 2024** 

## GENERIC MARKING DIAGRAM\*



XXXXX = Specific Device Code

A = Assembly Location
WL = Wafer Lot

Y = Year
WW = Work Week
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:		STYLE 3:	S	TYLE 4:	
	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
	BASE	2.	ANODE	2.	BASE. #1	2.	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER. #1	3.	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	
	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH		
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT)		
3.	,	3.	CATHODE	3.	COMMON DRAIN (OUTPUT)		
4.	,	4.	CATHODE	4.			
5.	DRAIN, #3	5.		5.	COMMON DRAIN (OUTPUT)		
6.	DRAIN, #3	6.		6.	COMMON DRAIN (OUTPUT)		
7.	DRAIN, #4		CATHODE	7.	COMMON DRAIN (OUTPUT)		
8.	DRAIN, #4		CATHODE	8.	SOURCE P-CH		
	GATE, #4		ANODE	9.	SOURCE P-CH		
10.	SOURCE, #4		ANODE	10.			
11.	GATE, #3		ANODE	11.			
12	SOURCE, #3	12.	ANODE	12.			
13.	GATE, #2	13.	ANODE	13.			
13. 14.	GATE, #2 SOURCE, #2	13. 14.	ANODE	14.	COMMON DRAIN (OUTPUT)		
13. 14. 15.	GATE, #2 SOURCE, #2 GATE, #1	13. 14. 15.	ANODE ANODE	14. 15.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
13. 14.	GATE, #2 SOURCE, #2	13. 14.	ANODE	14.	COMMON DRAIN (OUTPUT)		

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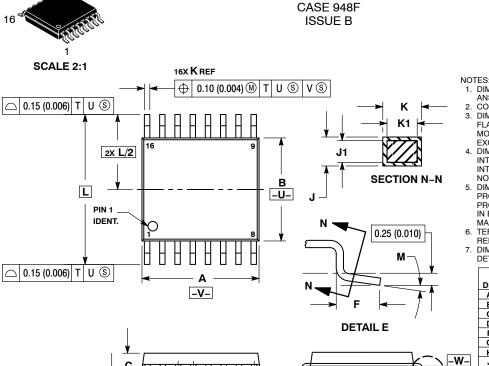
**DATE 19 OCT 2006** 



☐ 0.10 (0.004)

SEATING PLANE

D

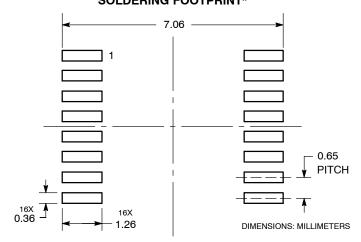


TSSOP-16 WB

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL
- IN TERLEAD FLASH OH PROTHOSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8°	0°	8 °

#### **RECOMMENDED** SOLDERING FOOTPRINT\*



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC** MARKING DIAGRAM\*



XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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**DETAIL E** 

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